Correction to: Room temperature ammonia gas sensor using Nd-doped SnO₂ thin films and its characterization

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The original version of the article (<https://doi.org/10.1007/s10854-020-03809-6>) was unfortunately published with errors in Table 2 and Fig. 9a. These errors are corrected in this article. The corrected table and figure are given below.

The original article can be found online at <https://doi.org/10.1007/s10854-020-03809-6>.

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Table 2 Structural properties

Nd concentration (%)	Film thickness (nm)	Grain size (nm)	Dislocation density $\times 10^{15}$ (lines/ m^2)	Strain	Lattice constants		Cell volume ($\text{\AA}^3$)
					a ($\text{\AA}$)	c ($\text{\AA}$)	
0	320	16	3.91	9.30×10^{-3}	4.6394	3.1561	67.93
1	343	19	2.77	8.20×10^{-3}	4.7004	3.3467	73.94
3	384	25	1.60	8.27×10^{-3}	4.7197	3.3680	75.02
5	410	33	0.91	8.27×10^{-3}	4.7197	3.5752	79.64

Fig. 9 a Response time (T_{res}) and recovery time (T_{rec}) of SnO_2 :Nd thin films (NH_3 gas of 25 ppm concentration)